

FIG. 1

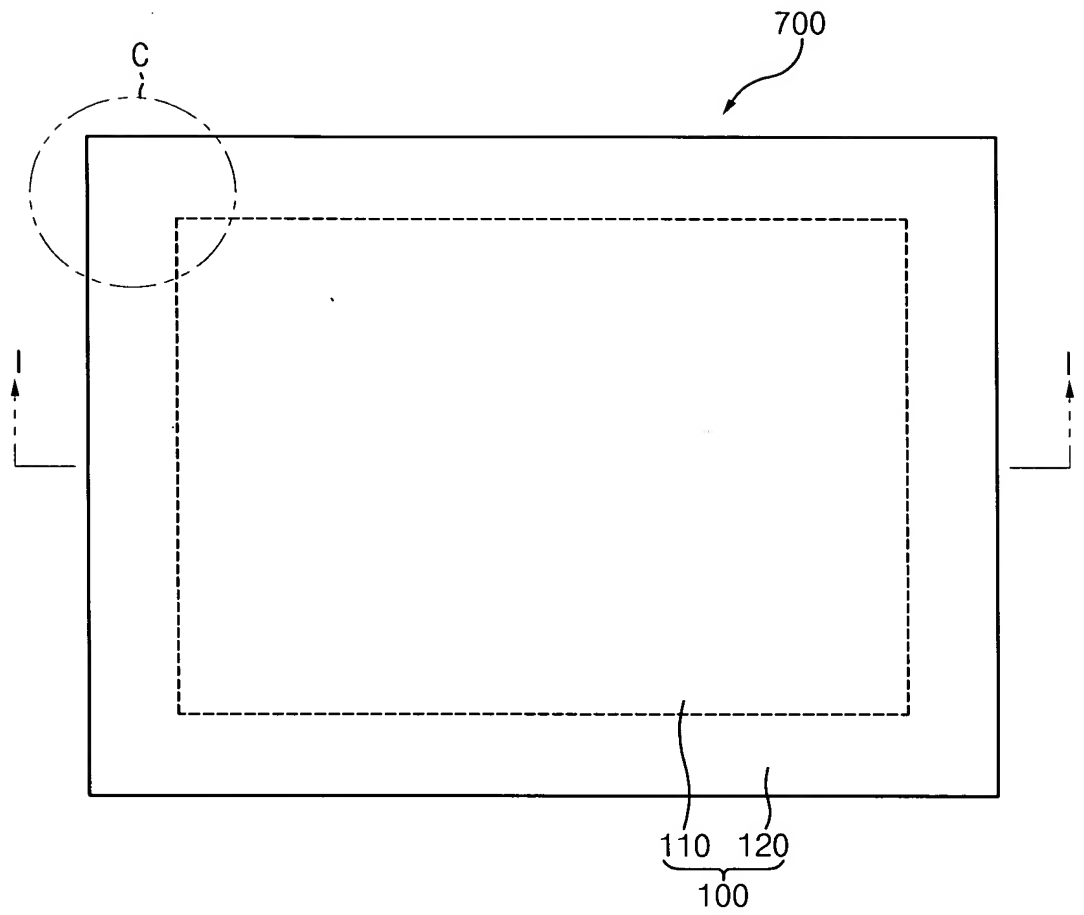


FIG. 2

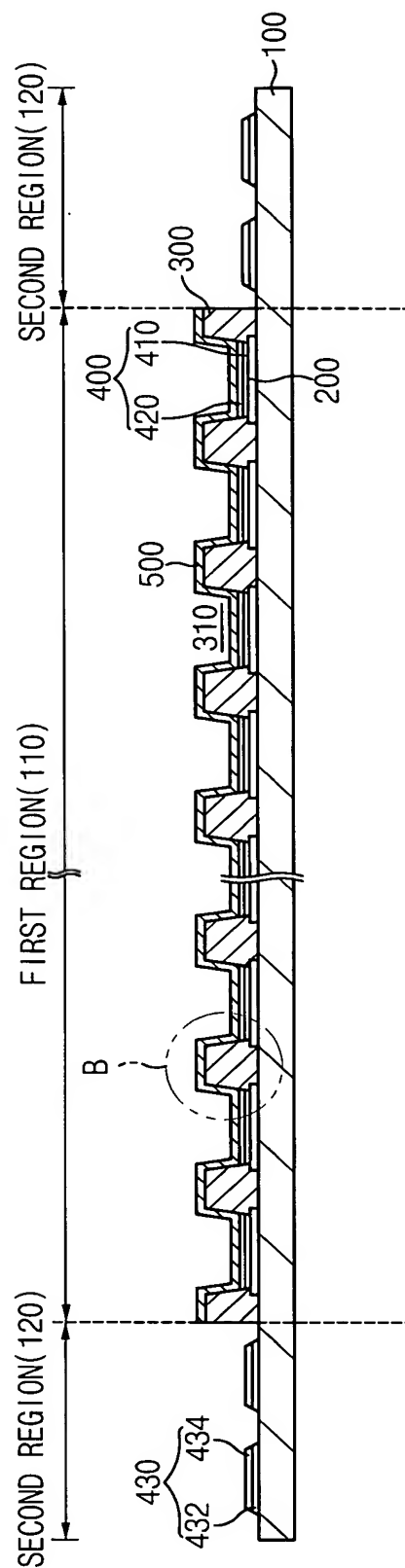


FIG. 3

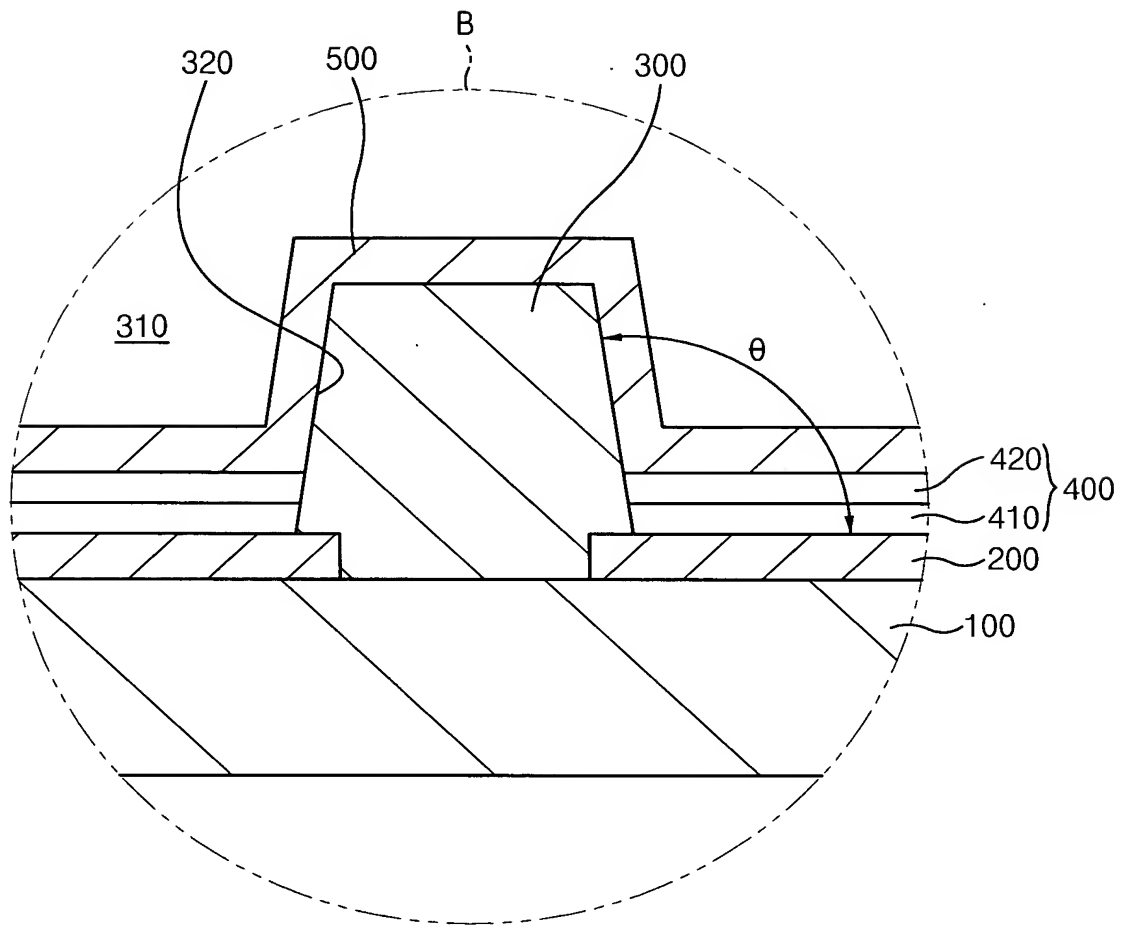




FIG. 5

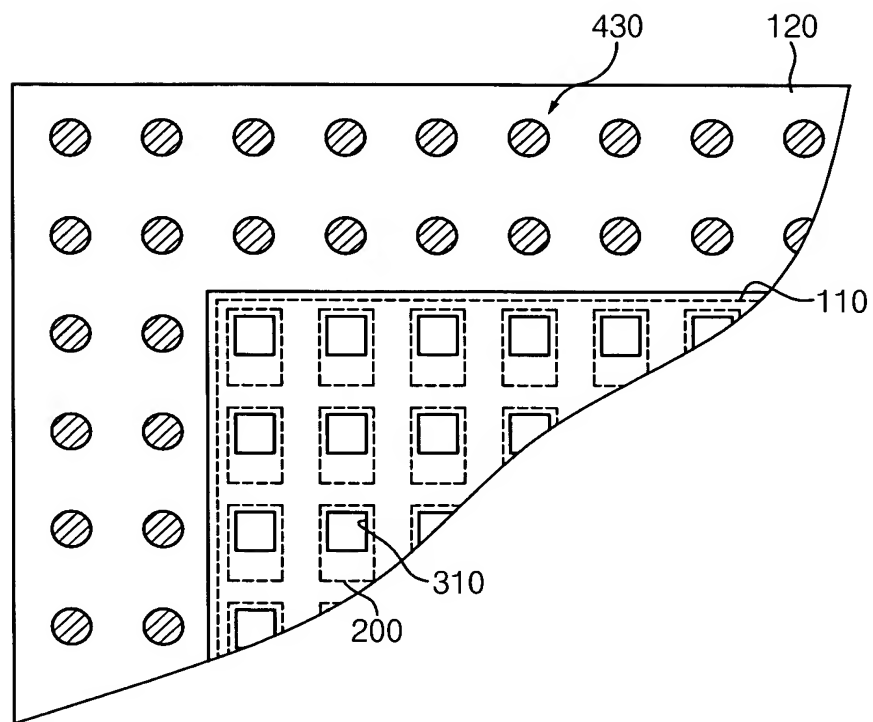


FIG. 6

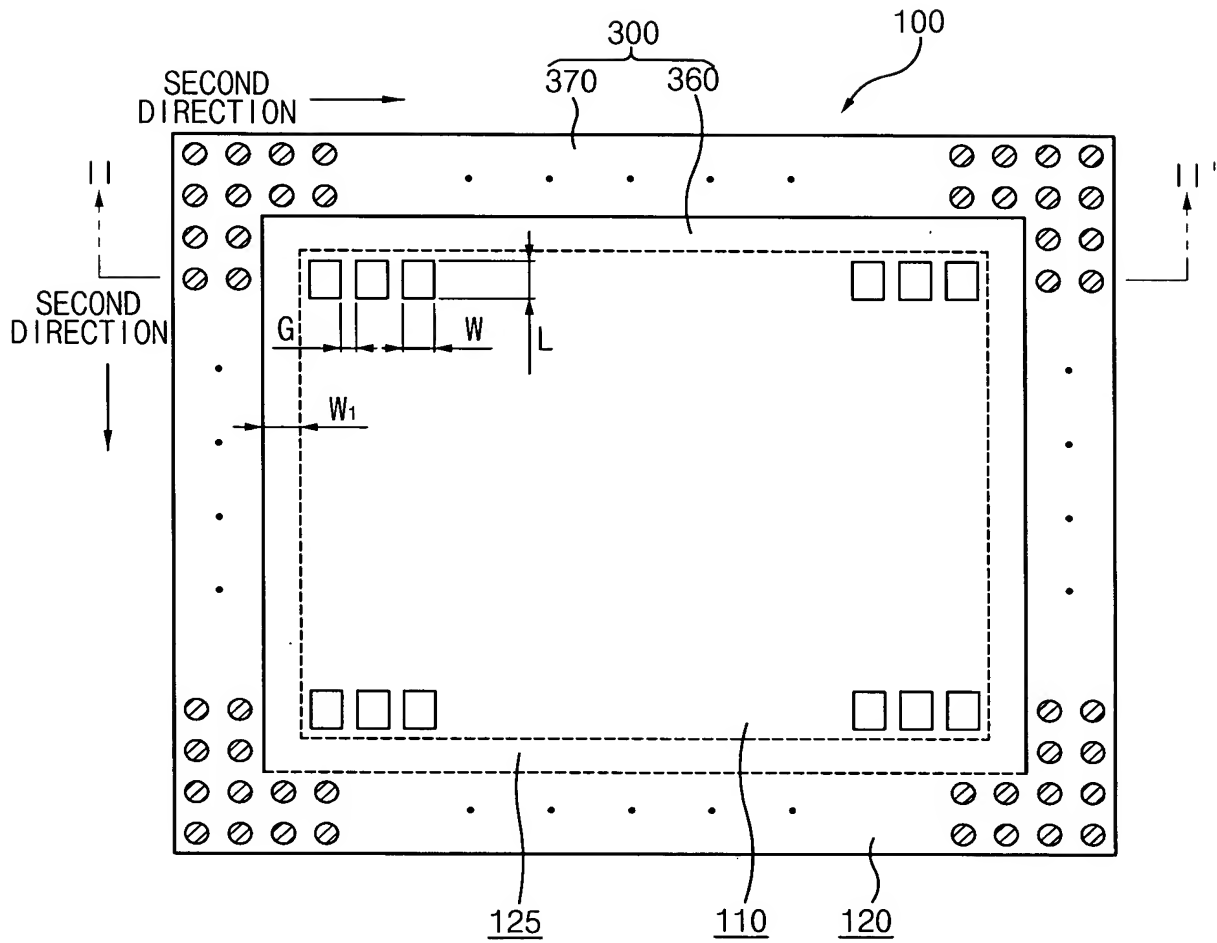


FIG. 7

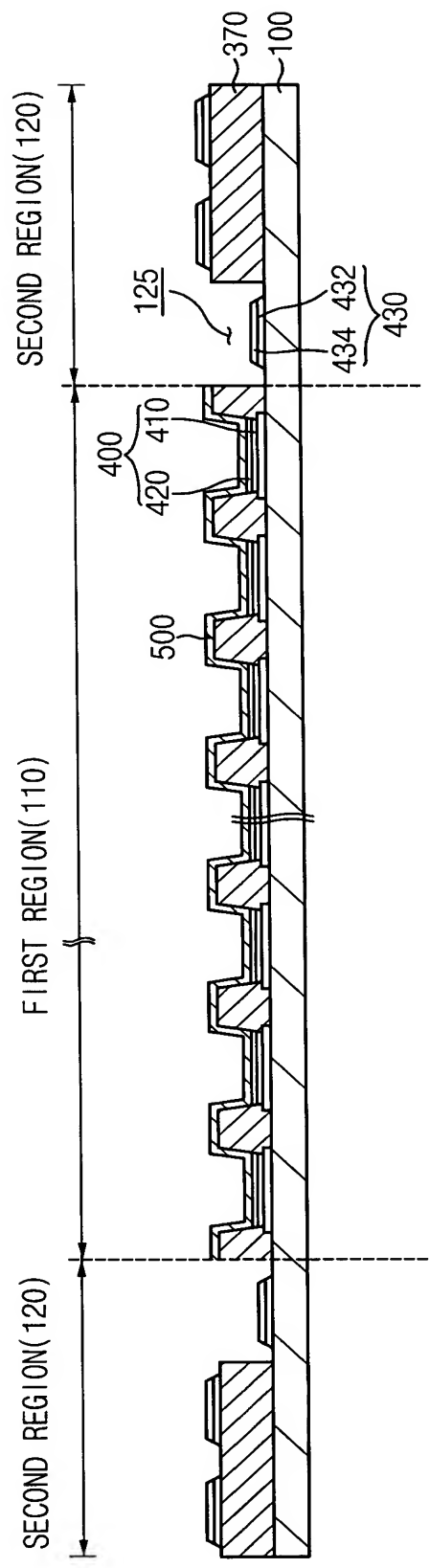


FIG. 8

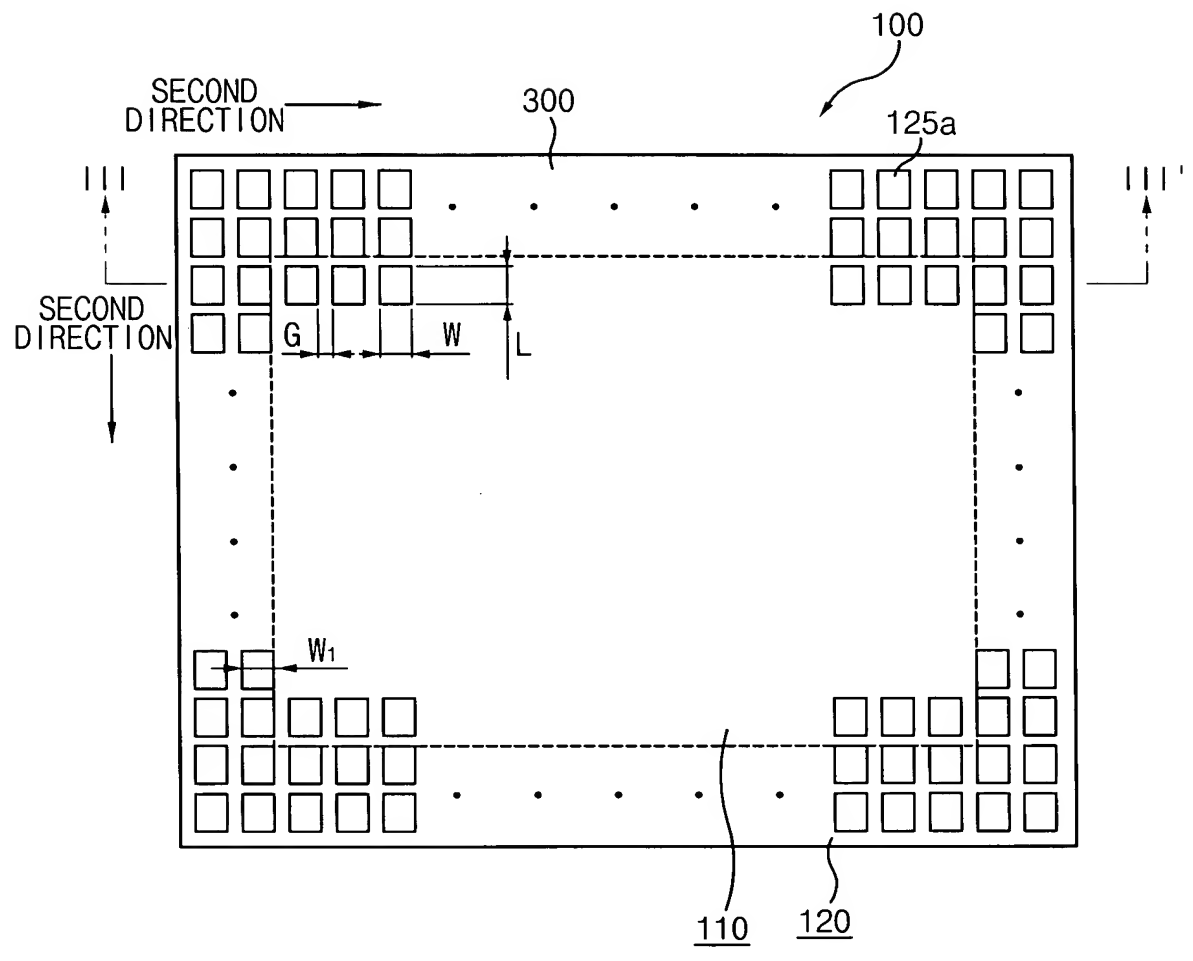




FIG. 9

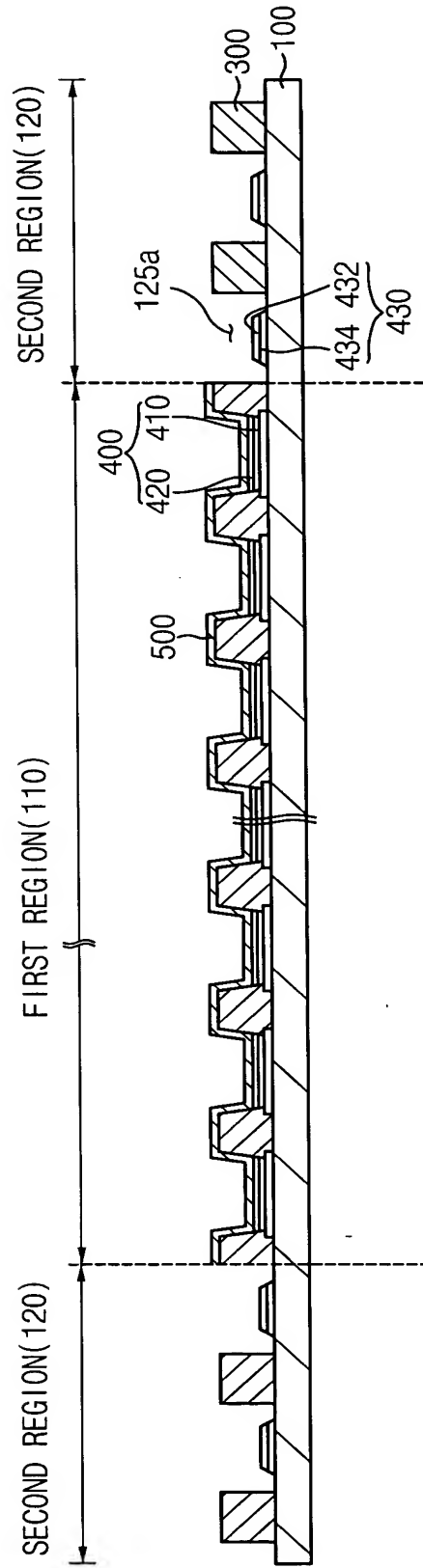


FIG. 10

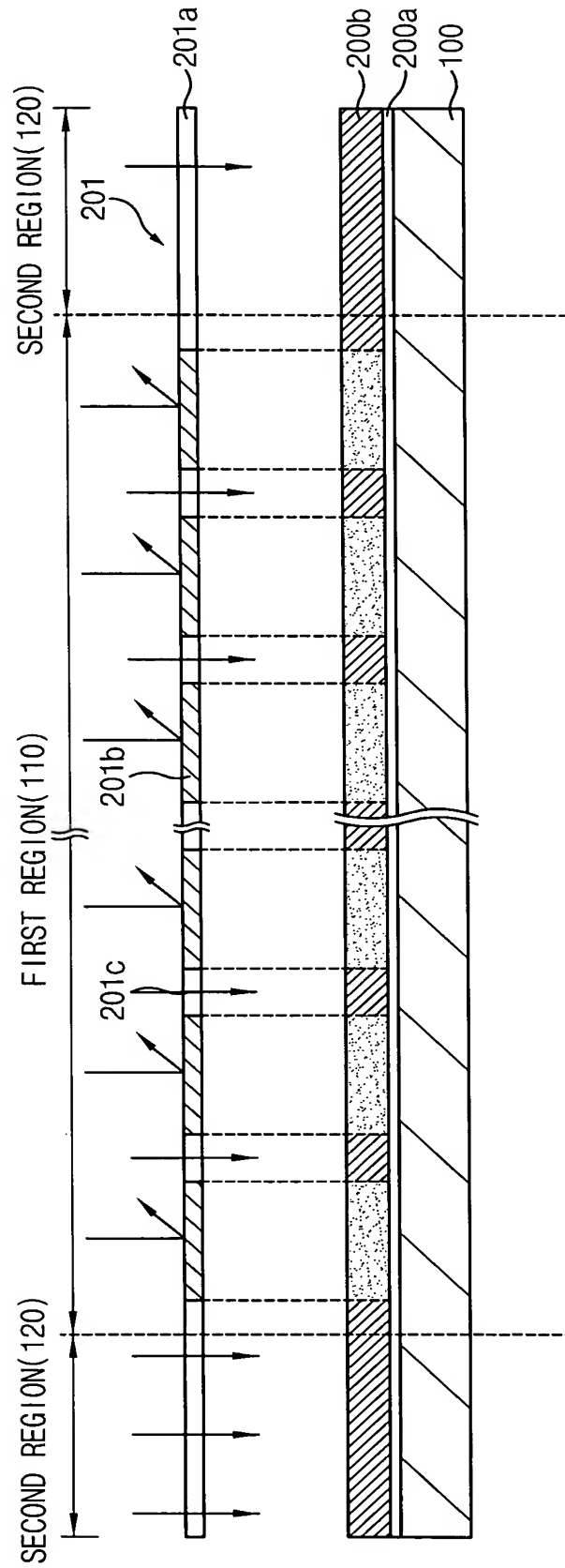


FIG. 11

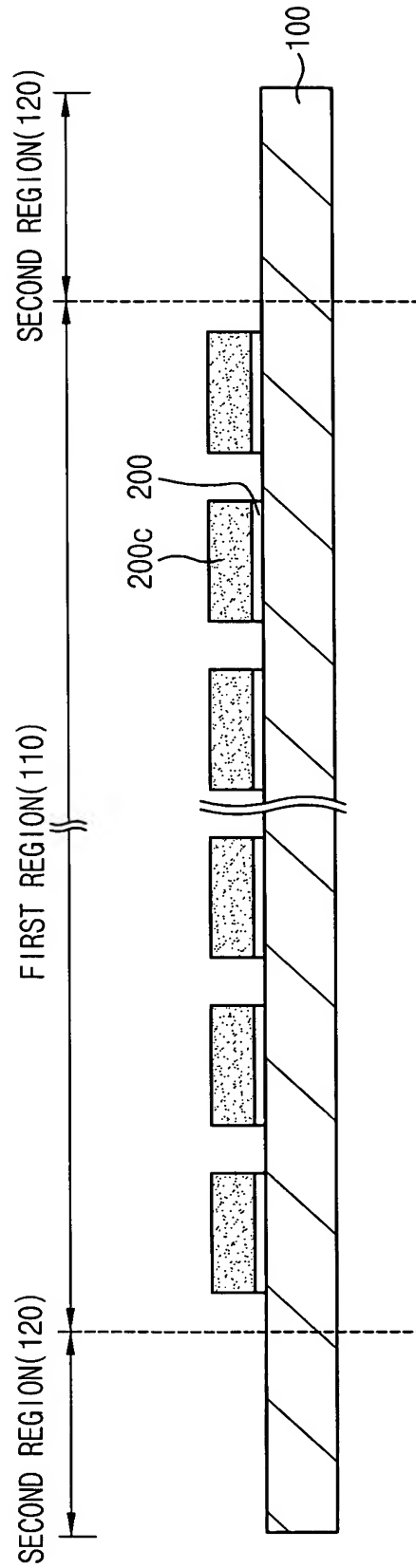


FIG. 12

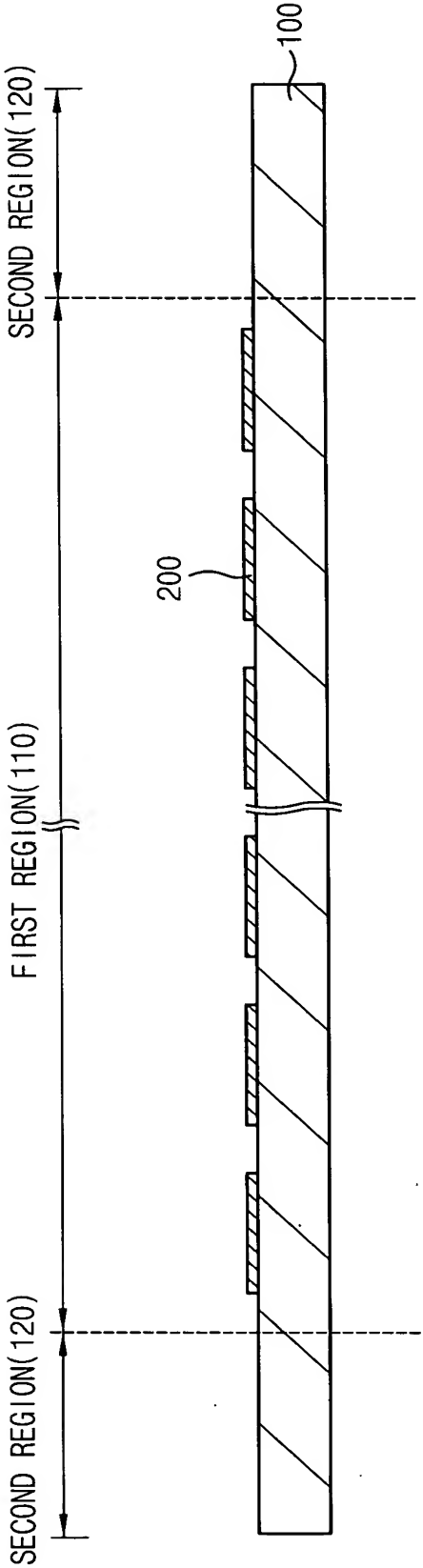


FIG. 13

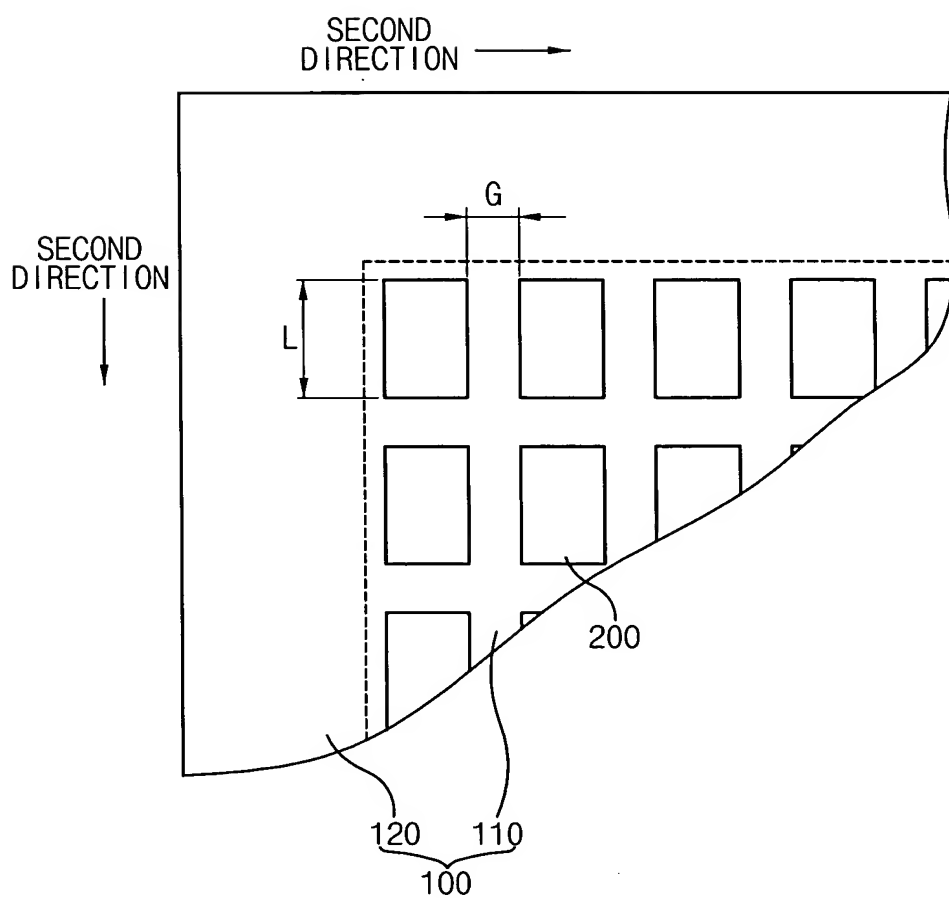


FIG. 14

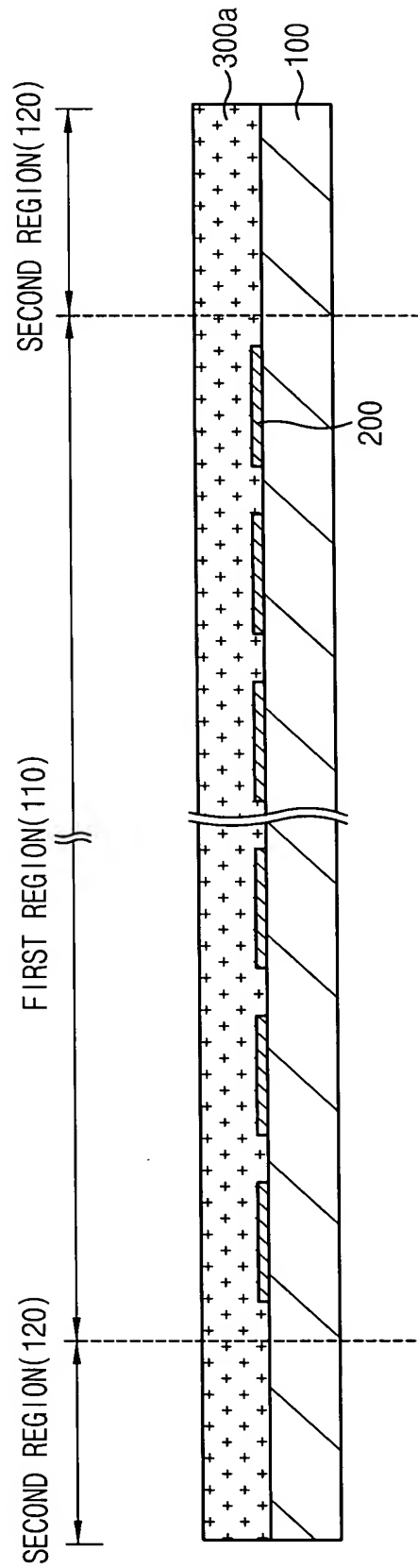


FIG. 1 is a cross-sectional view of a semiconductor device 100. The device is divided into a first region (110) and a second region (120). The first region (110) contains a series of vertical structures (301a, 301b, 301c) with horizontal arrows indicating a process flow. The second region (120) contains a series of vertical structures (300b) with horizontal arrows indicating a process flow. The device is labeled 100.

FIG. 16

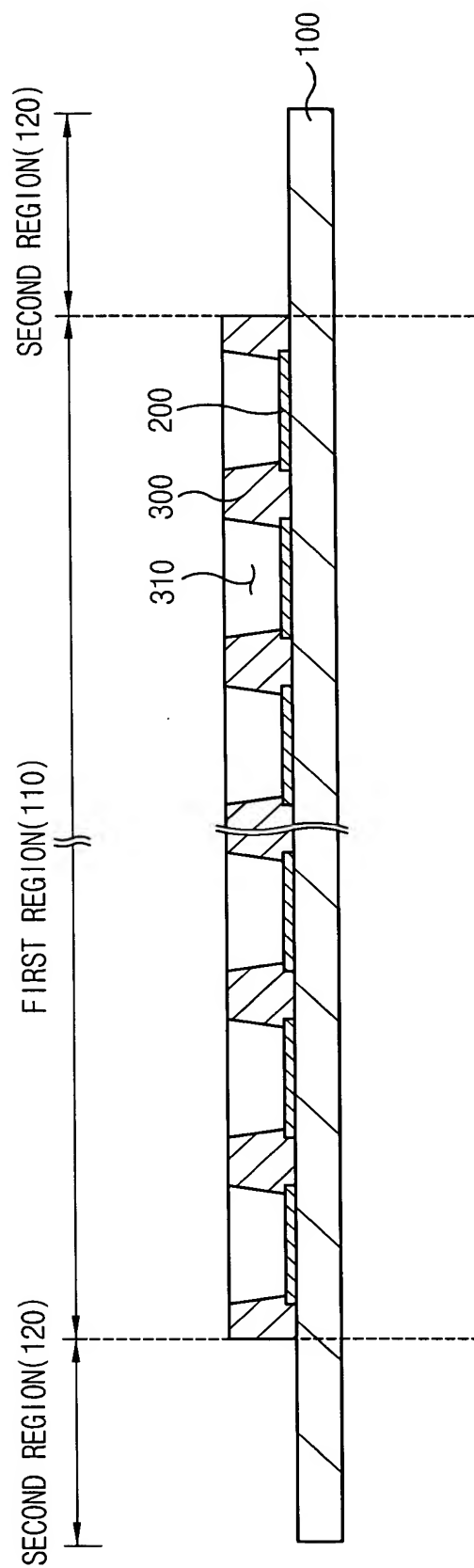




FIG. 17

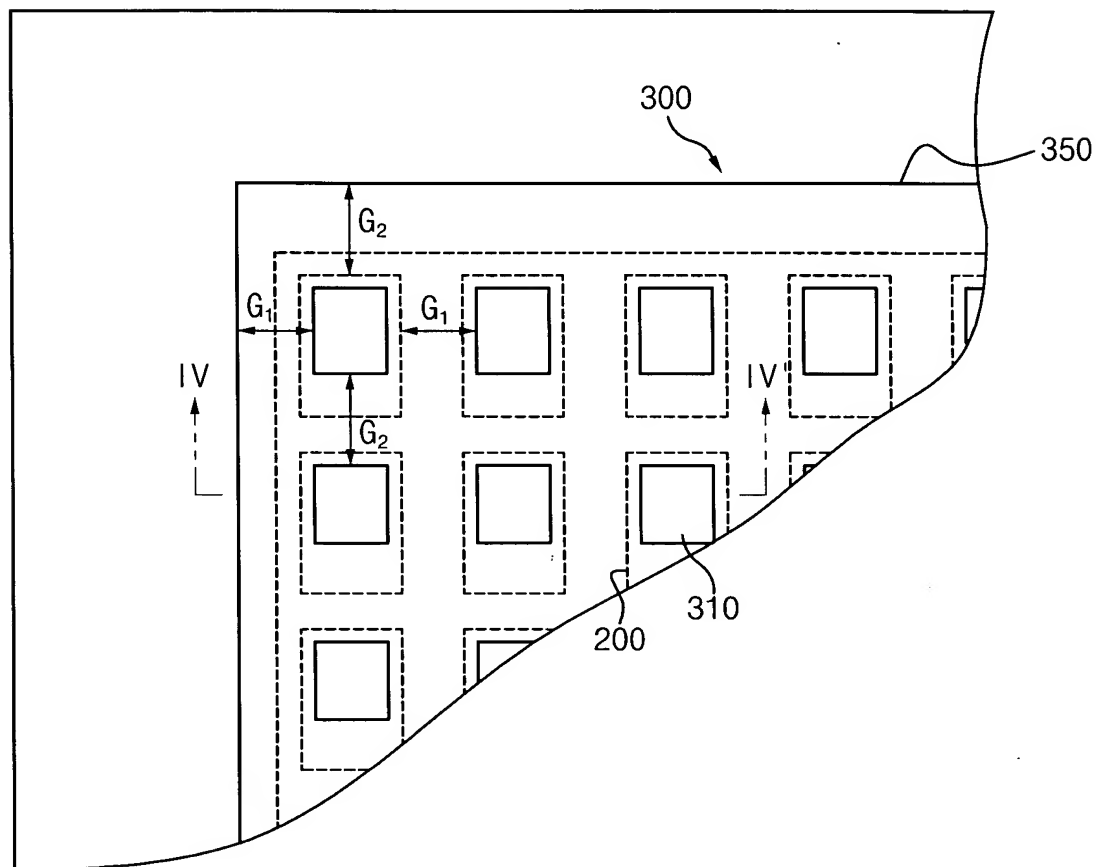


FIG. 18

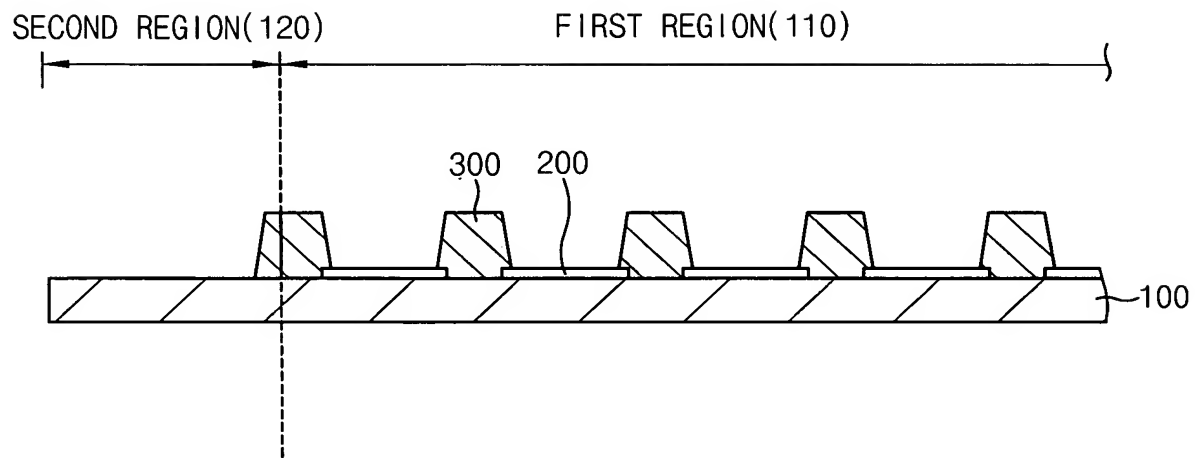


FIG. 19

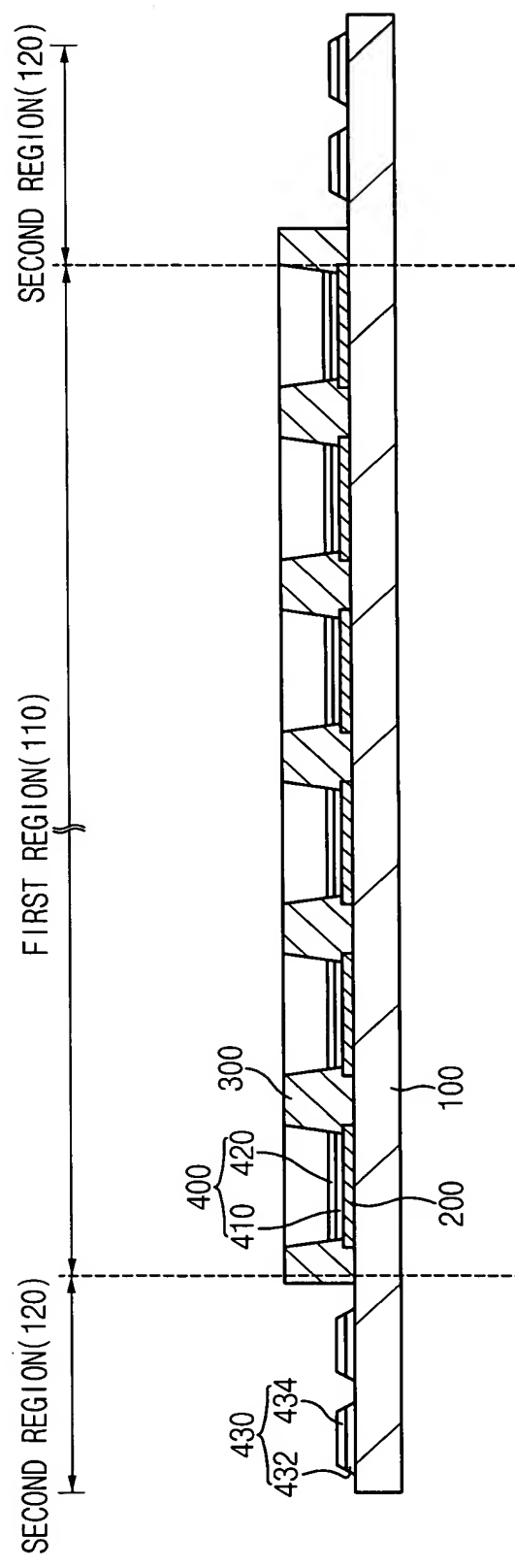


FIG. 20

